

N-Channel Enhancement Mode MOSFET

TDM3452

DESCRIPTION

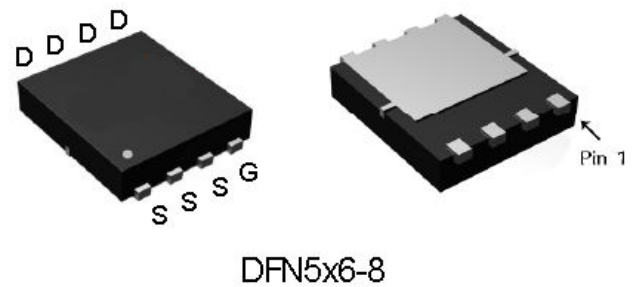
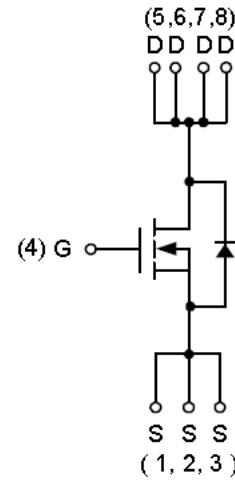
The TDM3452 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- RDS(ON) < 5.1mΩ @ VGS=4.5V
RDS(ON) < 3mΩ @ VGS=10V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



泰德半导体—提供样品, 技术支持 手机13418601901 QQ409545144

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current @ Continuous(Note 1)	I _D (T _c =25°C)	80	A
	I _D (T _c =100°C)	60	A
Drain Current @ Current-Pulsed (Note 2)	I _{DM} (T _c =25°C)	160	A
Maximum Power Dissipation (TA=25°C)	P _D	2.5	W
Maximum Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance,Junction-to-Ambient (Note 2)	R _{θJA}	50	°C/W
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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

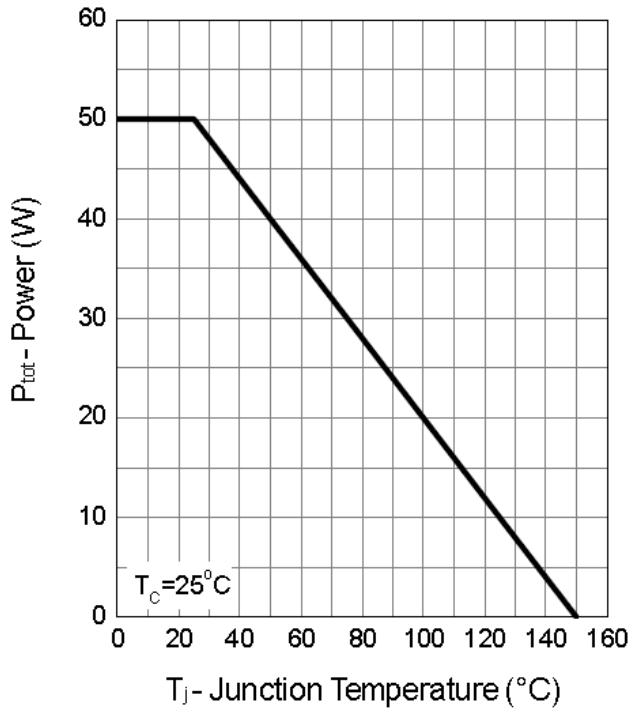
Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.4	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=15A$		3.9	5.1	$m\Omega$
		$V_{GS}=10V, I_D=20A$		2.5	3	$m\Omega$
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, F=1.0MHz$		1350		PF
Output Capacitance	C_{oss}			900		PF
Reverse Transfer Capacitance	C_{rss}			65		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=12V, R_L=2.1\Omega, V_{GEN}=10V, R_G=2.9\Omega, I_D=5.7A$		14.3		nS
Turn-on Rise Time	t_r			26		nS
Turn-Off Delay Time	$t_{d(off)}$			24		nS
Turn-Off Fall Time	t_f			4.4		nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=20A, V_{GS}=4.5V$		9.2		nC
Gate-Source Charge	Q_{gs}			6		nC
Gate-Drain Charge	Q_{gd}			2		nC
Body Diode Reverse Recovery Time	T_{rr}	$I_F=20A, di/dt=100A/\mu s$		21		nS
Body Diode Reverse Recovery Charge	Q_{rr}			6.3		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=20A$		0.81	1.1	V

NOTES:

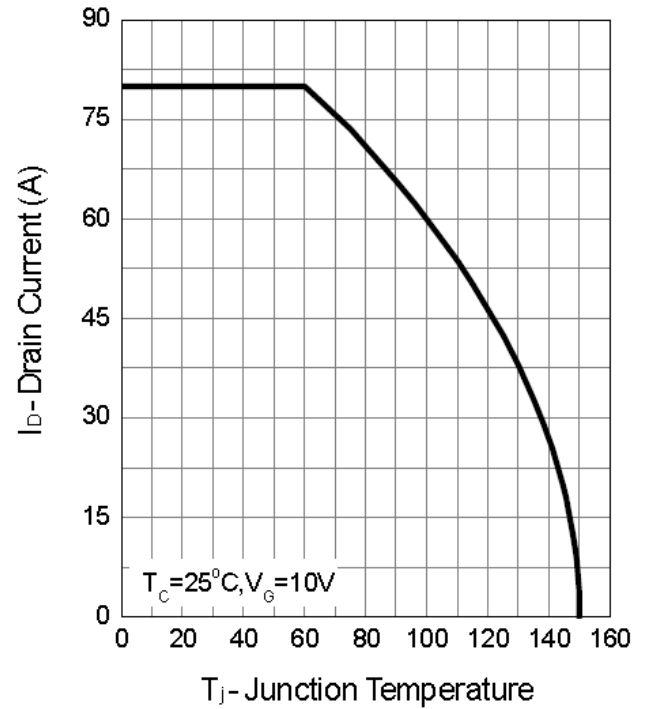
1. continue current is limited by bonding wire.
2. Pulse width limited by max. junction temperature.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing

Typical Operating Characteristics

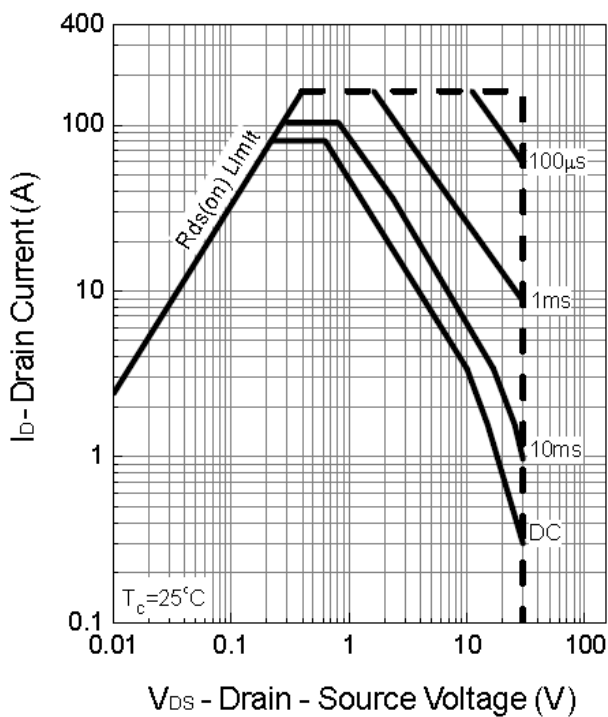
Power Dissipation



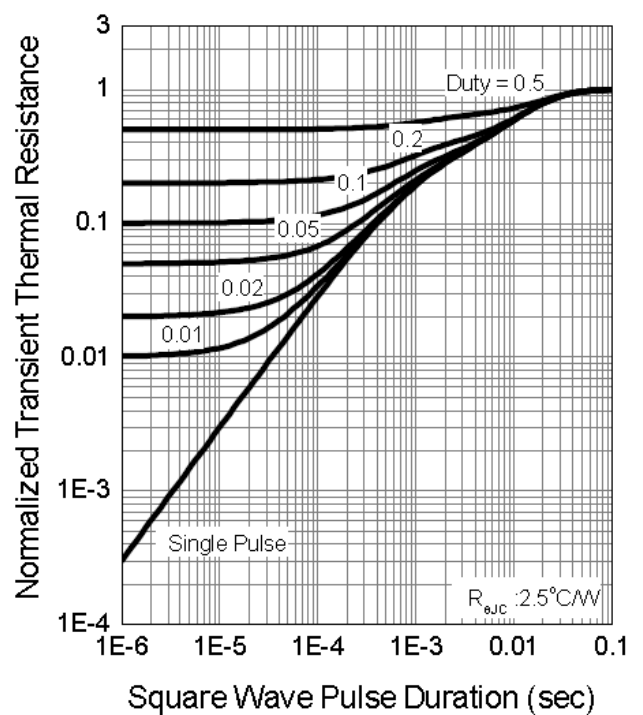
Drain Current



Safe Operation Area

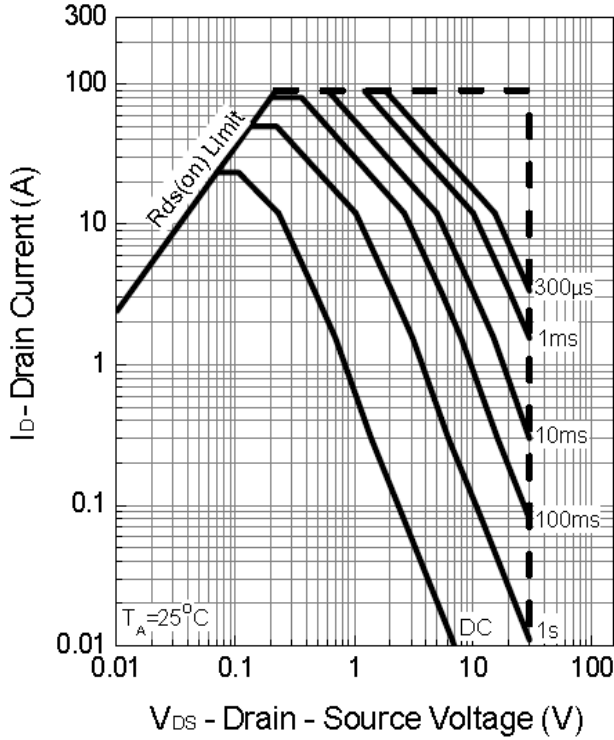


Thermal Transient Impedance

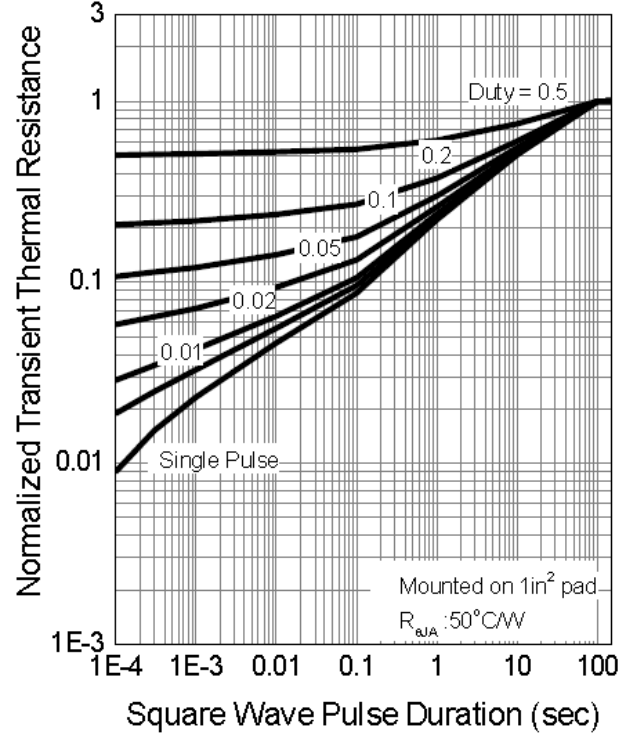


Typical Operating Characteristics(Cont.)

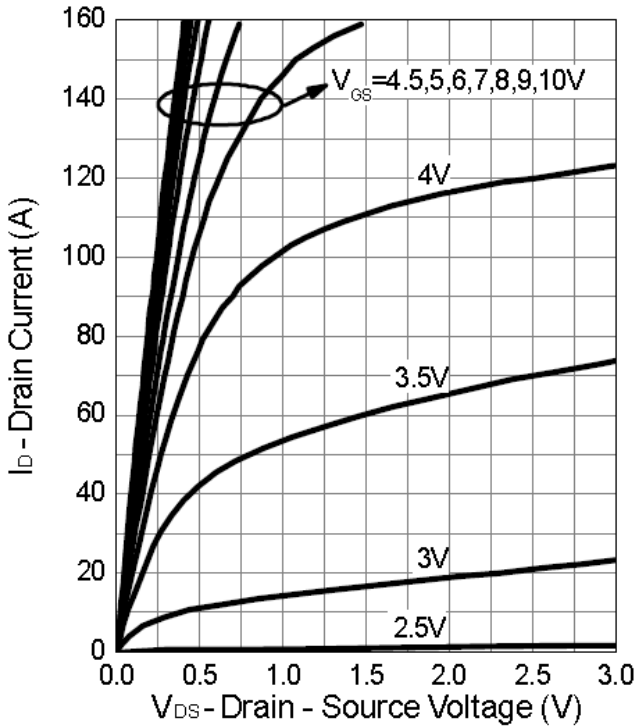
Safe Operation Area



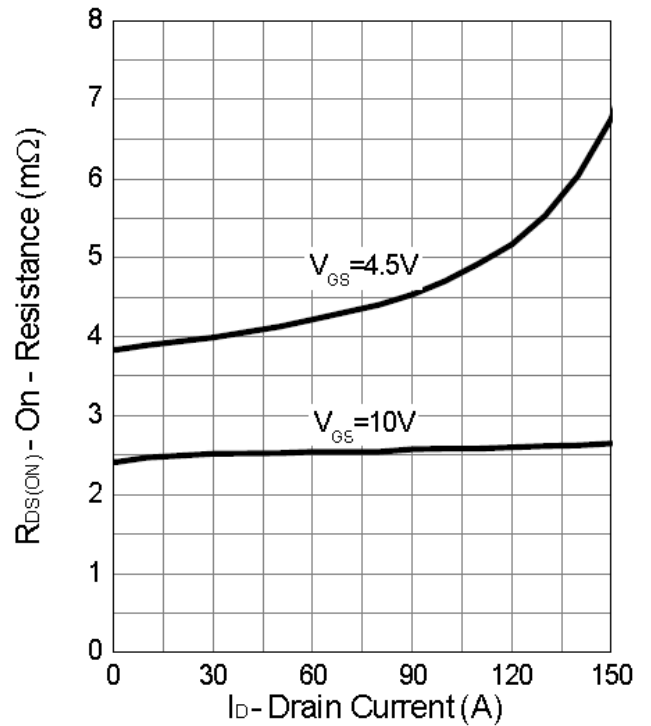
Thermal Transient Impedance



Output Characteristics

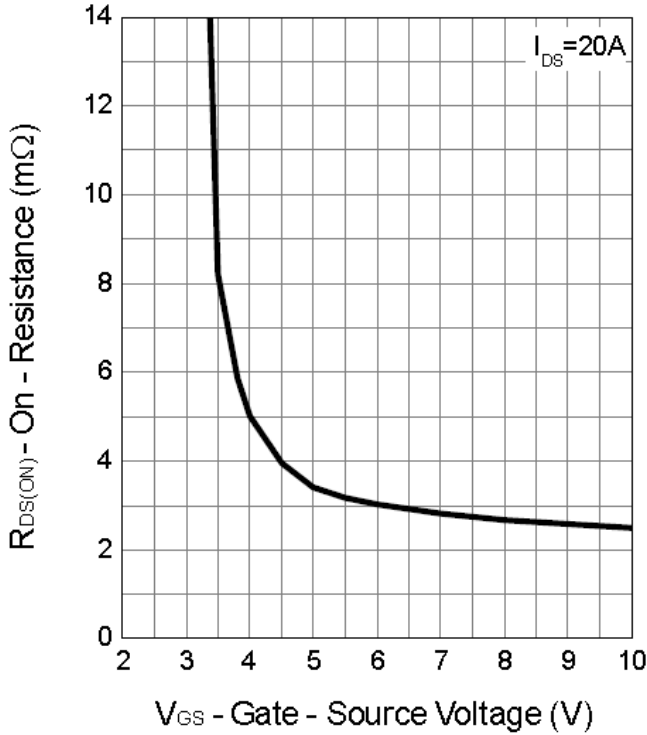


Drain-Source On Resistance

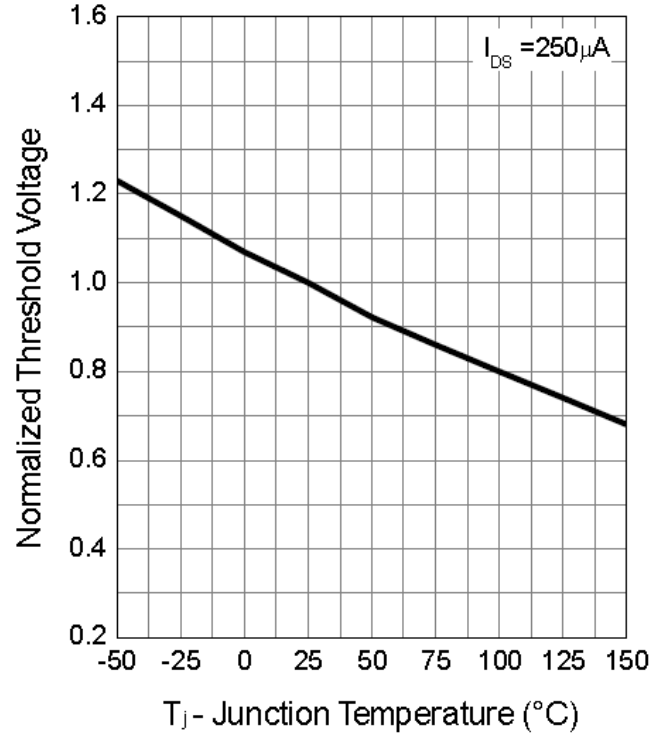


Typical Operating Characteristics (Cont.)

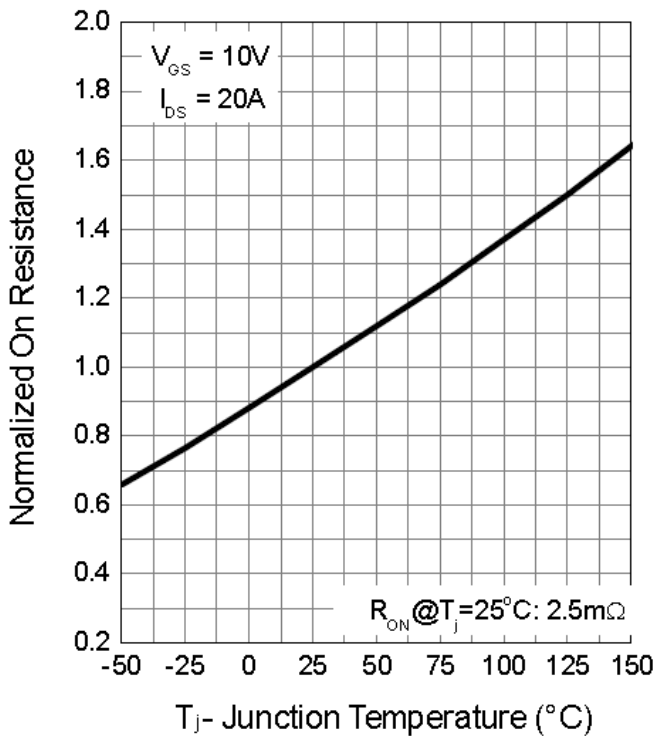
Gate-Source On Resistance



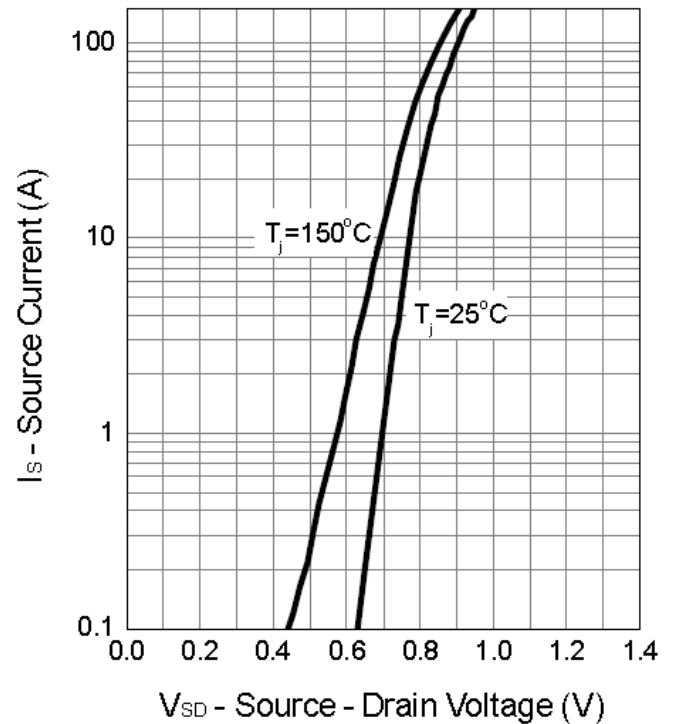
Gate Threshold Voltage



Drain-Source On Resistance

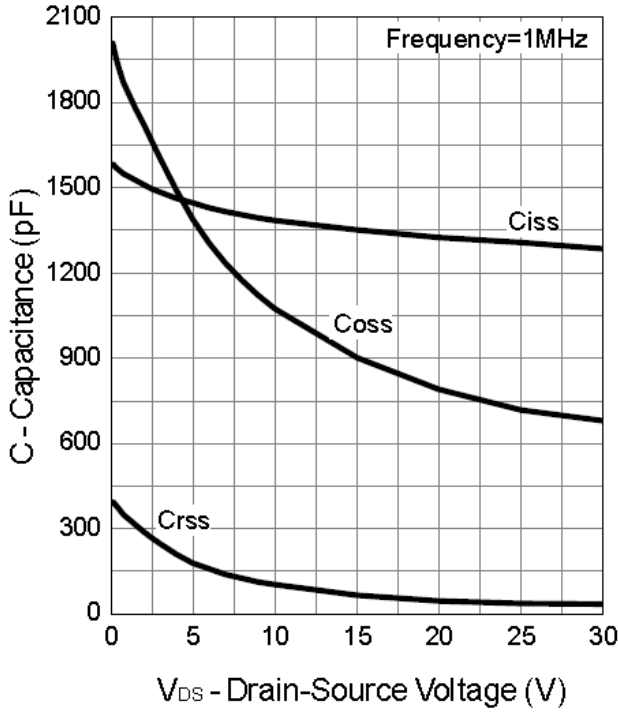


Source-Drain Diode Forward

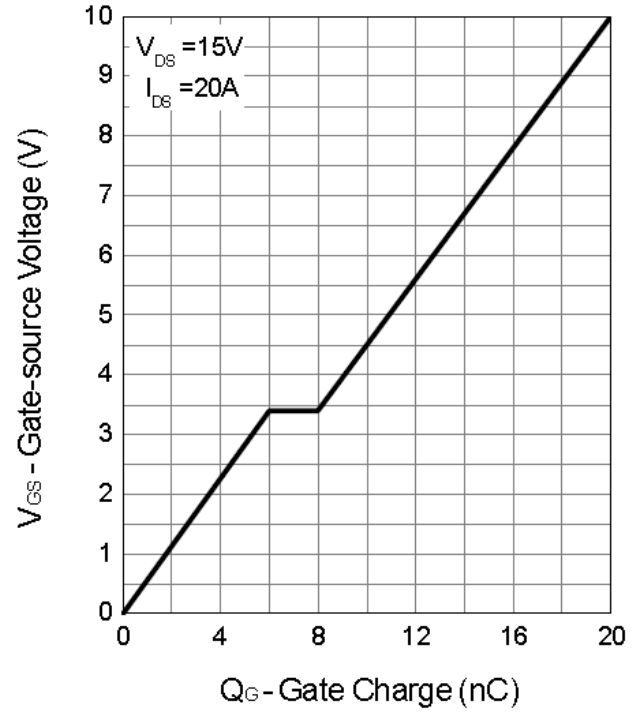


Typical Operating Characteristics (Cont.)

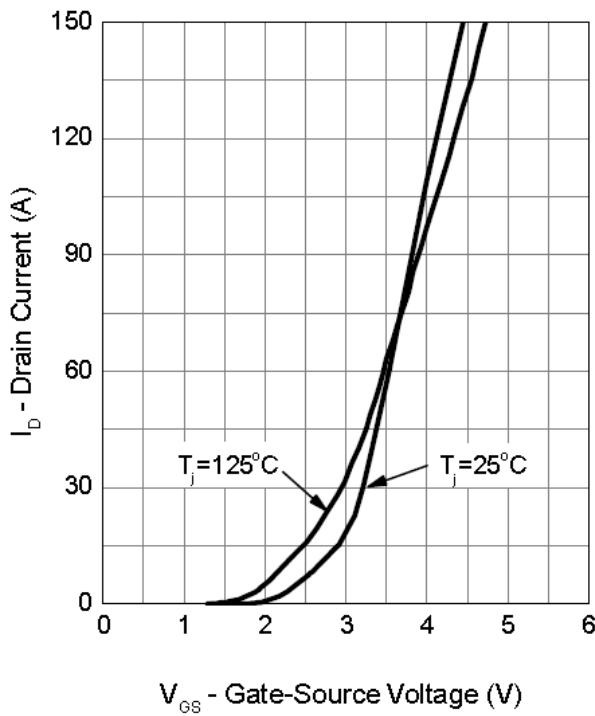
Capacitance



Gate Charge



Transfer Characteristics



Design Notes